We Claim:

水.	1	1. An arc chamber of an ion implanter system comprising:
mor	2	an arc chamber enclosure for an electron emissive source, said source extending
7	3	into said arc chamber enclosure through a wall of said arc chamber enclosure, said wall
	4	through which said source extends comprising an insulator material surrounding said
1	5	source.
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	1	2. The arc chamber of Claim 1 wherein said insulator material is a high
	2	temperature ceramic material.
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	1	3. The arc chamber of Claim 2 wherein said insulator material is
Li Li	2	selected from the group consisting of alumina and boron nitride.
L.	1	4. The arc chamber of Claim 3 wherein said insulator material is boron
# 	2	nitride.
NA P	1	5. The arc chamber of Glaffin 1 wherein a substantial portion of said wall
n, 02	2	through which said source extends into the arc chamber comprises an insulator material.